## **SPTECH Silicon NPN Power Transistor**

**MJE15030** 

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 150V(Min)
- · High Current Gain-Bandwidth Product-
- :  $f_T = 30MHz(Min)@ I_C = 0.5A$
- DC current gain -
  - : h<sub>FE</sub> = 40 (Min) @I<sub>C</sub>= 3.0 A
  - : h<sub>FE</sub> = 20 (Min) @I<sub>C</sub>= 4.0 A
- Complement to Type MJE15031

#### **APPLICATIONS**

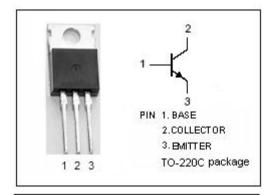
 Designed for use as high–frequency drivers in audio amplifiers.

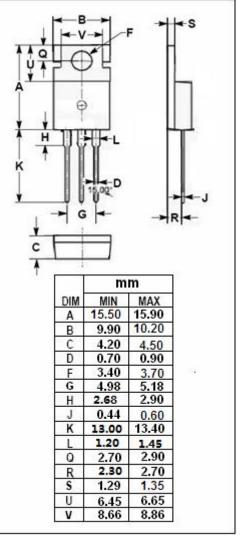
### ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	150		
V <sub>CEO</sub>	Collector-Emitter Voltage	tage 150		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current -Continuous	8	Α	
I <sub>CM</sub>	Collector Current-Peak	16	А	
I <sub>B</sub>	Base Current	2	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25℃	50		
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-65~150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	2.5	°C/W
R <sub>th j-a</sub>	j-a Thermal Resistance,Junction to Ambient		°C/W





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**MJE15030** 

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
VCEO(SUS)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA ;I <sub>B</sub> = 0	150		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A ;I <sub>B</sub> = 0.1A		0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V		1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0		10	μ <b>А</b>
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 150V; I <sub>B</sub> = 0		0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		10	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 2V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 2V	40		
h <sub>FE-3</sub>	DC Current Gain	Ic= 3A ; Vc== 2V	40		
h <sub>FE-4</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 2V	20		
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.5A;V <sub>CE</sub> = 10V; f <sub>test</sub> = 10MHz	20		MHz

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